

L Number	Hits	Search Text	DB	Time stamp
1	50	(US-6020595-\$ or US-5920296-\$ or US-5500572-\$ or US-5212426-\$ or US-6340859-\$ or US-6218771-\$ or US-6140701-\$ or US-6084341-\$ or US-6031322-\$ or US-6031250-\$ or US-5910701-\$ or US-5864147-\$ or US-5844252-\$ or US-5550426-\$ or US-5319233-\$ or US-5285079-\$ or US-6369505-\$ or US-6369496-\$ or US-6356014-\$ or US-6351059-\$ or US-6211608-\$ or US-6181060-\$ or US-6075315-\$ or US-5633560-\$ or US-5347292-\$ or US-5229331-\$).did. or (US-5191217-\$ or US-5142184-\$ or US-5055077-\$ or US-5012482-\$ or US-5007873-\$ or US-5396096-\$ or US-6140687-\$ or US-5898198-\$ or US-6340962-\$ or US-5214346-\$ or US-5918137-\$ or US-5461242-\$ or US-4742380-\$ or US-6028322-\$ or US-5965898-\$ or US-4968639-\$).did. or (JP-09259746-\$ or JP-11102637-\$ or JP-09063467-\$ or JP-09063466-\$ or JP-09035622-\$ or JP-10074473-\$ or JP-62229880-\$).did. or (EP-651417-\$).did.	USPAT; JPO; DERWENT	2002/10/25 09:24
2	0	ogata.in. and gate adj electrode and field adj emission	JPO	2002/10/25 09:26
3	72	ogata.in. and gate adj electrode	JPO	2002/10/25 11:00
4	302	(mos or mosfet or cmosfet or cmos or nmos or nmosfet or pmosfet or pmos).ti,ab,clm. and (width or wide or wider) near6 gate near6 drain near6 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 11:03
5	70	(mos or mosfet or cmosfet or cmos or nmos or nmosfet or pmosfet or pmos).ti,ab,clm. and (width or wide or wider) near3 gate near3 drain near3 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 11:03
6	1	(mos or mosfet or cmosfet or cmos or nmos or nmosfet or pmosfet or pmos).ti,ab,clm. and wider near3 gate near3 drain near3 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 11:56
7	2	jp-09063467\$-\$).did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 11:56
8	2765	((315/169.1) or (315/169.2) or (315/167) or (315/309) or (313/336) or (257/146) or (257/153)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 13:56
9	163	((315/169.1) or (315/169.2) or (315/167) or (315/309) or (313/336) or (257/146) or (257/153)).CCLS.) and (field adj emission or field-emission) near3 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 13:56
10	97	((315/169.1) or (315/169.2) or (315/167) or (315/309) or (313/336) or (257/146) or (257/153)).CCLS.) and (field adj emission or field-emission) near3 source) and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 13:59
11	4	((315/169.1) or (315/169.2) or (315/167) or (315/309) or (313/336) or (257/146) or (257/153)).CCLS.) and (field adj emission or field-emission) near3 source) and gate) and electrode near6 channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/25 14:00

-	0	jp-963467\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/18 20:55
-	0	jp-40963467\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/18 20:56
-	0	"9-63467"	JPO	2002/05/18 20:58
-	0	"963467"	JPO	2002/05/18 20:58
-	0	"963467"\$3	JPO	2002/05/18 20:58
-	4	cold adj electron adj emitting adj element and hirano.in. and ito.in.	JPO	2002/05/18 22:06
-	57881	yamaguchi.in. hirakawa.in. and tomita.in.	JPO	2002/05/18 21:02
-	1	yamaguchi.in. and hirakawa.in. and tomita.in.	JPO	2002/05/18 21:05
-	1	mosfet adj type adj electron adj emission adj element	JPO	2002/05/18 21:06
-	1	jp-07130281\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/18 21:36
-	7109	315/\$6.ccls.	JPO	2002/05/18 22:07
-	52381	315/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/05/18 22:07
-	1832	field adj emission adj cathode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 11:29
-	25	field adj emission adj cathode and gate and (field adj effect adj transistor or fet) and source and drain and channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 11:39
-	174	(cold adj cathode or field adj emission adj cathode) and 257/\$7.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 11:53
-	135	(cold adj cathode or field adj emission adj cathode and extraction adj gate) and 257/\$7.ccls.	USPAT	2002/05/19 11:53
-	135	(cold adj cathode or field adj emission adj cathode and extraction adj gate and channel) and 257/\$7.ccls.	USPAT	2002/05/19 12:04
-	0	cold adj cathode and field adj emission adj (display or cathode) and extraction adj gate and channel and 257/\$7.ccls.	USPAT	2002/05/19 11:59
-	1046	(cold adj cathode or field adj emission adj cathode and extraction adj gate and channel) and 313/\$7.ccls.	USPAT	2002/05/19 12:05
-	1045	(cold adj cathode or field adj emission adj cathode and extraction adj gate and channel and silicon adj substrate) and 313/\$7.ccls.	USPAT	2002/05/19 12:06
-	1045	(cold adj cathode or field adj emission adj cathode and extraction adj gate and channel and silicon adj substrate and (field adj effect adj transistor or fet)) and 313/\$7.ccls.	USPAT	2002/05/19 12:27
-	634	(cold adj cathode or field adj emission adj cathode and extraction adj gate and channel and silicon adj substrate and (field adj effect adj transistor or fet)) and 315/\$7.ccls.	USPAT	2002/05/19 12:28

-	1	(cold adj cathode or field adj emission adj cathode) and extraction adj gate and channel and silicon adj substrate and (field adj effect adj transistor or fet) and 315/\$7.ccls.	USPAT	2002/05/19 12:28
-	0	(cold adj cathode or field adj emission adj cathode) and extraction adj gate and channel and silicon adj substrate and (field adj effect adj transistor or fet) and 313/\$7.ccls.	USPAT	2002/05/19 12:29
-	1	(cold adj cathode or field adj emission adj cathode) and extraction adj gate and channel and silicon adj substrate and (field adj effect adj transistor or fet) and (313/\$7.ccls. or 315/\$6.ccls. or 257/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:30
-	34	(US-5142184-\$ or US-5191217-\$ or US-5212426-\$ or US-5229331-\$ or US-5633560-\$ or US-6075315-\$ or US-6181060-\$ or US-6211608-\$ or US-6340859-\$ or US-6351059-\$ or US-6356014-\$ or US-6369496-\$ or US-6369505-\$ or US-5285079-\$ or US-5319233-\$ or US-5550426-\$ or US-5844252-\$ or US-5910701-\$ or US-6031250-\$ or US-6031322-\$ or US-6084341-\$ or US-6218771-\$ or US-6140701-\$ or US-5500572-\$ or US-5007873-\$ or US-5012482-\$).did. or (US-5055077-\$).did. or (JP-10074473-\$ or JP-09063467-\$ or JP-09063466-\$ or JP-11102637-\$ or JP-09035622-\$ or JP-09259746-\$).did. or (EP-651417-\$).did.	USPAT; JPO; DERWENT	2002/05/19 12:40
-	14	((US-5142184-\$ or US-5191217-\$ or US-5212426-\$ or US-5229331-\$ or US-5633560-\$ or US-6075315-\$ or US-6181060-\$ or US-6211608-\$ or US-6340859-\$ or US-6351059-\$ or US-6356014-\$ or US-6369496-\$ or US-6369505-\$ or US-5285079-\$ or US-5319233-\$ or US-5550426-\$ or US-5844252-\$ or US-5910701-\$ or US-6031250-\$ or US-6031322-\$ or US-6084341-\$ or US-6218771-\$ or US-6140701-\$ or US-5500572-\$ or US-5007873-\$ or US-5012482-\$).did. or (US-5055077-\$).did. or (JP-10074473-\$ or JP-09063467-\$ or JP-09063466-\$ or JP-11102637-\$ or JP-09035622-\$ or JP-09259746-\$).did. or (EP-651417-\$).did.) and (p-type or p adj type or p-silicon or p-doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:37
-	2	((US-5142184-\$ or US-5191217-\$ or US-5212426-\$ or US-5229331-\$ or US-5633560-\$ or US-6075315-\$ or US-6181060-\$ or US-6211608-\$ or US-6340859-\$ or US-6351059-\$ or US-6356014-\$ or US-6369496-\$ or US-6369505-\$ or US-5285079-\$ or US-5319233-\$ or US-5550426-\$ or US-5844252-\$ or US-5910701-\$ or US-6031250-\$ or US-6031322-\$ or US-6084341-\$ or US-6218771-\$ or US-6140701-\$ or US-5500572-\$ or US-5007873-\$ or US-5012482-\$).did. or (US-5055077-\$).did. or (JP-10074473-\$ or JP-09063467-\$ or JP-09063466-\$ or JP-11102637-\$ or JP-09035622-\$ or JP-09259746-\$).did. or (EP-651417-\$).did.) and (p-type or p adj type or p-silicon or p-doped)) and source and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:37

-	8	((US-5142184-\$ or US-5191217-\$ or US-5212426-\$ or US-5229331-\$ or US-5633560-\$ or US-6075315-\$ or US-6181060-\$ or US-6211608-\$ or US-6340859-\$ or US-6351059-\$ or US-6356014-\$ or US-6369496-\$ or US-6369505-\$ or US-5285079-\$ or US-5319233-\$ or US-5550426-\$ or US-5844252-\$ or US-5910701-\$ or US-6031250-\$ or US-6031322-\$ or US-6084341-\$ or US-6218771-\$ or US-6140701-\$ or US-5500572-\$ or US-5007873-\$ or US-5012482-\$).did. or (US-5055077-\$).did. or (JP-10074473-\$ or JP-09063467-\$ or JP-09063466-\$ or JP-11102637-\$ or JP-09035622-\$ or JP-09259746-\$).did. or (EP-651417-\$).did.) and focus\$4	USPAT; JPO; DERWENT	2002/05/19 12:43
-	2	((US-5142184-\$ or US-5191217-\$ or US-5212426-\$ or US-5229331-\$ or US-5633560-\$ or US-6075315-\$ or US-6181060-\$ or US-6211608-\$ or US-6340859-\$ or US-6351059-\$ or US-6356014-\$ or US-6369496-\$ or US-6369505-\$ or US-5285079-\$ or US-5319233-\$ or US-5550426-\$ or US-5844252-\$ or US-5910701-\$ or US-6031250-\$ or US-6031322-\$ or US-6084341-\$ or US-6218771-\$ or US-6140701-\$ or US-5500572-\$ or US-5007873-\$ or US-5012482-\$).did. or (US-5055077-\$).did. or (JP-10074473-\$ or JP-09063467-\$ or JP-09063466-\$ or JP-11102637-\$ or JP-09035622-\$ or JP-09259746-\$).did. or (EP-651417-\$).did.) and focus\$4	USPAT; JPO; DERWENT	2002/05/19 12:45
-	0	cold adj cathode and (fet or field adj effect adj transistor) and field adj emission and extract\$3 near4 gate and source and drain and channel and silicon near4 substrate and (ldd or lightly-doped or lightly adj doped)	USPAT; JPO; DERWENT	2002/05/19 12:48
-	0	cold adj cathode and (fet or field adj effect adj transistor) and field adj emission and extract\$3 near4 gate and source and drain and channel and silicon near4 substrate and (ldd or lightly-doped or lightly adj doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:49
-	0	cold adj cathode and field adj emission and extract\$3 near4 gate and source and drain and channel and silicon near4 substrate and (ldd or lightly-doped or lightly adj doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:49
-	13	(cold near2 cathode or field adj emission adj cathode) and gate and source and drain and channel and silicon near4 substrate and (ldd or lightly-doped or lightly adj doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:53
-	2	("5550435").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:59
-	6952	lightly adj doped adj drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:02

-	2155	lightly adj doped adj drain.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:15
-	0	lightly adj doped adj drain.ti,ab. and cold adj cathode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:03
-	0	lightly adj doped adj drain.ti,ab. and field adj emission adj cathode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:04
-	0	(ldd or lightly-doped adj drain or lightly adj doped adj drain) and (cold adj cathode or field adj emission adj cathode).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:08
-	0	jp-6055616\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:11
-	2	jp-60055616\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:11
-	1	lightly adj doped adj drain.ti,ab. and phosphorus near10 arsenic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:17
-	0	lightly adj doped adj drain near10 phosphorus near10 arsenic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:17
-	0	(ldd or lightly adj doped adj drain) near10 phosphorus near10 arsenic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:18
-	1	(ldd or lightly adj doped adj drain) and phosphorus near10 arsenic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:27
-	2	("5550435").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 14:07
-	1750	ldd and phosphorus same arsenic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 14:08
-	16	ldd and phosphorus same arsenic same different near3 diffusion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 14:09
-	0	cold adj cathode and (field adj effect adj transistor or fet) and (gate near4 different near4 width)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 14:58

-	200	(field adj effect adj transistor or fet) and (gate near4 different near4 width)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 14:59
-	2	(field adj effect adj transistor or fet) and (gate near4 different near4 width) and (hot near3 electron) and (ldd or lightly adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 15:00
-	10	(field adj effect adj transistor or fet) and (gate near4 different near4 width) and (hot near3 electron)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 15:01
-	1068	width near6 gate near6 (variable or different)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 15:08
-	137	width near6 gate near6 (variable or different) and 257/\$6.ccls. and (ldd or lightly-doped drain or lightly adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 15:09
-	90	width near3 gate near3 (variable or different) and 257/\$6.ccls. and (ldd or lightly-doped drain or lightly adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 15:11
-	27	width near3 gate near3 (variable or different) and 257/\$6.ccls. and (ldd or lightly-doped drain or lightly adj doped adj drain) and plan adj view	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 15:19
-	329	257/249.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 15:24
-	6	257/249.ccls. and (ldd or lightly adj doped adj drain or lightly-doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 15:21
-	15	257/249.ccls. and gate adj width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 15:29
-	114	257/401.ccls. and gate adj width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 15:36
-	13	257/401.ccls. and gate near3 (width or wider) near4 source near4 drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 15:43
-	2	jp-60022375\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 16:37
-	2	("5550435").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 16:55

-	1002	shield\$3 near4 gate near4 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 16:56
-	3849	shield\$3 adj electrode	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 16:56
-	556	shield\$3 adj electrode and (257/\$6.ccls. or 313/\$6.ccls. or 315/\$6.ccls.)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 16:57
-	3	shield adj electrode near10 gate and (257/\$6.ccls. or 313/\$6.ccls. or 315/\$6.ccls.) and (cold adj cathode or field adj emission)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 17:31
-	697	(electrode near3 (shield or shielding) near3 gate)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 17:38
-	398	(electrode near3 (shield or shielding) near3 gate) and channel	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 18:26
-	0	(electrode near3 (shield or shielding) near3 gate) and channel and flat adj type adj display	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 18:27
-	13	(electrode near3 (shield or shielding) near3 gate) and channel and flat adj2 display	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 19:57
-	0	jp-0963467\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 20:53
-	2	((("5550435") or ("5396096")).PN.	USPÄT	2002/05/19 21:09
-	2	jp-62229880\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 21:18
-	0	jp-64061953\$-\$\$.did.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 21:18
-	0	jp-6461953\$-\$\$.did.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 21:18
-	4003	((315/169.1) or (315/169.2) or (315/167) or (315/309) or (313/336) or (257/249) or (257/401) or (257/146) or (257/153)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 21:55
-	12	((315/169.1) or (315/169.2) or (315/167) or (315/309) or (313/336) or (257/249) or (257/401) or (257/146) or (257/153)).CCLS.) and shield near3 electrode near3 gate	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 21:38

-	238	(257/10).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 22:06
-	0	(257/10 and shield\$3).CCLS.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 22:07
-	18	((257/10).CCLS.) and shield\$3	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/19 22:07
-	13	drain near3 p-type near4 n-type same (punch adj through or punch-through)	USPÄT	2002/05/20 08:11
-	50	(US-6340859-\$ or US-5396096-\$ or US-6218771-\$ or US-6031322-\$ or US-6084341-\$ or US-6031250-\$ or US-5910701-\$ or US-5864147-\$ or US-5844252-\$ or US-6140687-\$ or US-5550426-\$ or US-5898198-\$ or US-5319233-\$ or US-5285079-\$ or US-6369505-\$ or US-6369496-\$ or US-6356014-\$ or US-6351059-\$ or US-5347292-\$ or US-5229331-\$ or US-5191217-\$ or US-5142184-\$ or US-6211608-\$ or US-6140701-\$ or US-6181060-\$ or US-6075315-\$).did. or (US-5633560-\$ or US-5055077-\$ or US-5012482-\$ or US-5007873-\$ or US-5920296-\$ or US-6020595-\$ or US-5500572-\$ or US-5212426-\$ or US-6340962-\$ or US-5214346-\$ or US-5918137-\$ or US-5461242-\$ or US-4742380-\$ or US-6028322-\$ or US-5965898-\$ or US-4968639-\$).did. or (JP-09063467-\$ or JP-09259746-\$ or JP-09035622-\$ or JP-10074473-\$ or JP-09063466-\$ or JP-11102637-\$ or JP-62229880-\$).did. or (EP-651417-\$).did.	USPAT; JPO; DERWENT	2002/10/24 18:07
-	2	(lightly-doped adj drain or lightly adj doped adj drain or ldd) near6 surround\$3 near6 (heavily-doped adj drain or heavily adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/24 18:10